

Description

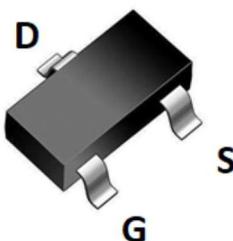
PECJ N-channel Enhancement Mode Power MOSFET

Features

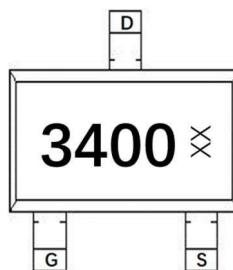
- 30V,5.8A
- $R_{DS(ON)} < 26m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 32m\Omega$ @ $V_{GS} = 4.5V$
- $R_{DS(ON)} < 50m\Omega$ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

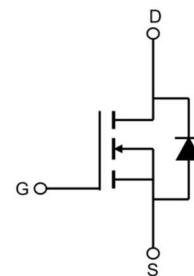
- Load Switch
- PWM Application
- Power management



SOT-23-3L top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
3400	PECJ3400A	TAPING	SOT-23-3L	7inch	3000	180000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	A
		$T_A = 100^\circ C$	A
I_{DM}	Pulsed Drain Current ^{note1}	23.2	A
P_D	Power Dissipation	$T_A = 25^\circ C$	W
$R_{\theta JA}$	Thermal Resistance, Junction to Case	92	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5	0.9	1.4	V
$R_{DS(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{GS}=10\text{V}$, $I_D=4.2\text{A}$	-	20.4	26	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=4\text{A}$	-	23	32	
		$V_{GS}=2.5\text{V}$, $I_D=1\text{A}$	-	30	50	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	702	-	pF
C_{oss}	Output Capacitance		-	66	-	pF
C_{rss}	Reverse Transfer Capacitance		-	52	-	pF
Q_g	Total Gate Charge	$V_{DS}=15\text{V}$, $I=4\text{A}$, $V_{GS}=4.5\text{V}$	-	4.8	-	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15\text{V}$, $I_D=4\text{A}$, $R_{\text{GEN}}=3\Omega$, $V_{GS}=4.5\text{V}$	-	12	-	ns
t_r	Turn-on Rise Time		-	52	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current		-	-	5.8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_s=5.8\text{A}$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

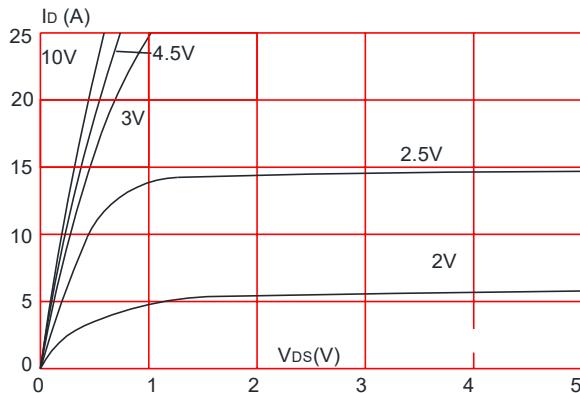


Figure 3: On-resistance vs. Drain Current

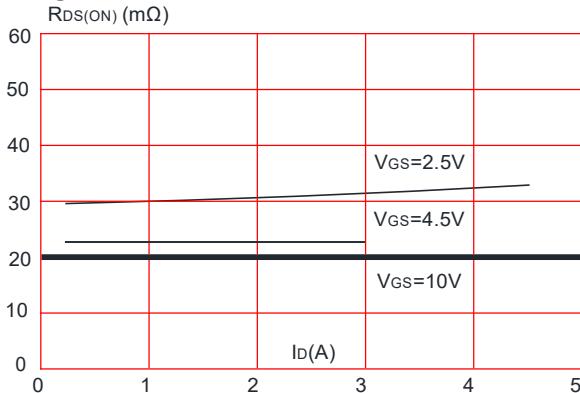


Figure 5: Gate Charge Characteristics

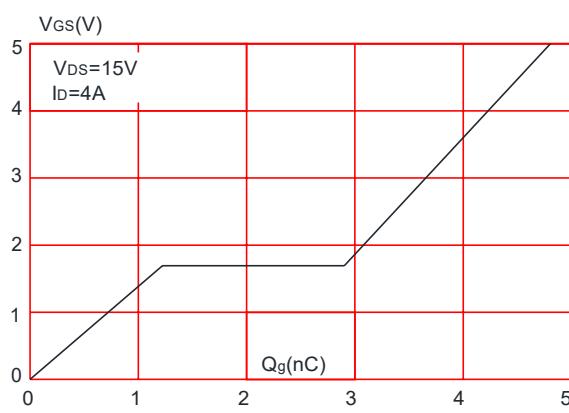


Figure 2: Typical Transfer Characteristics

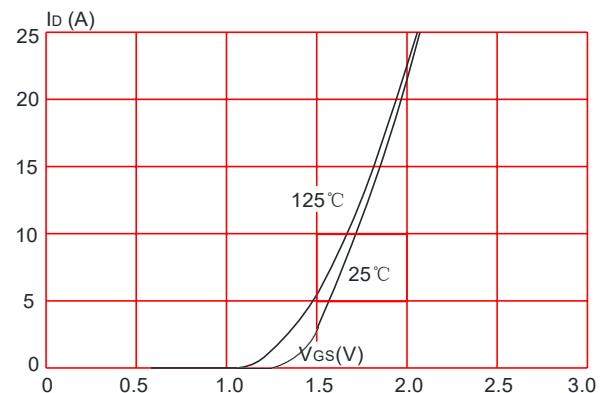


Figure 4: Body Diode Characteristics

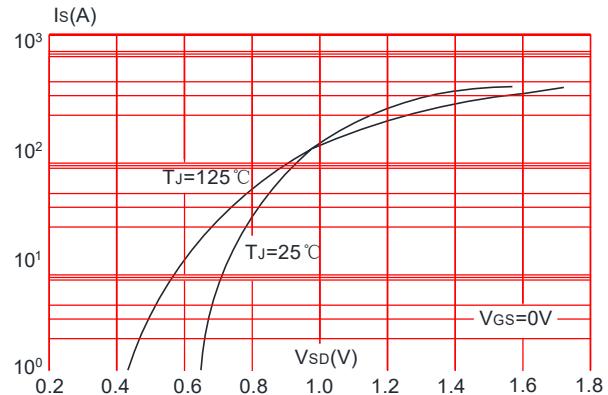


Figure 6: Capacitance Characteristics

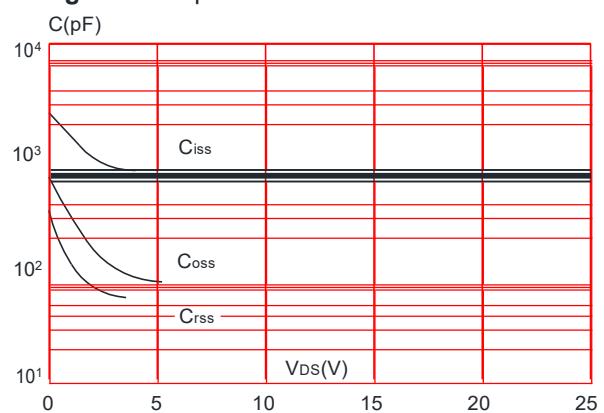


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

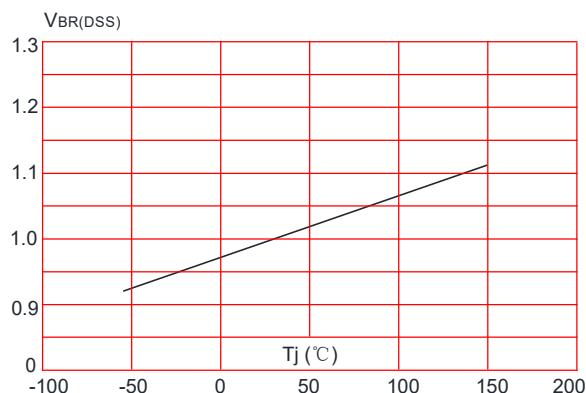


Figure 9: Maximum Safe Operating Area

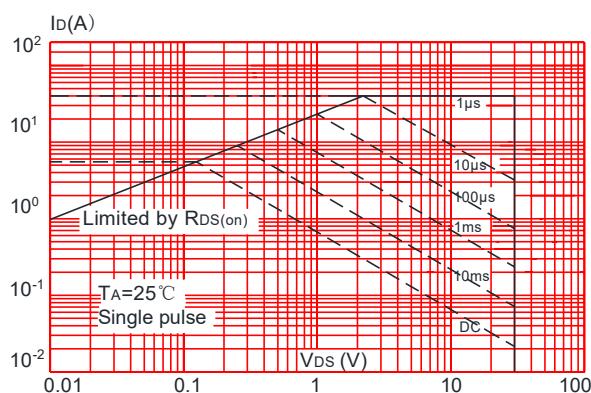


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

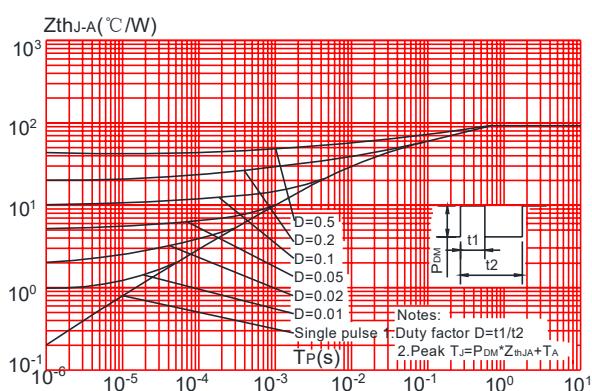


Figure 8: Normalized on Resistance vs. Junction Temperature

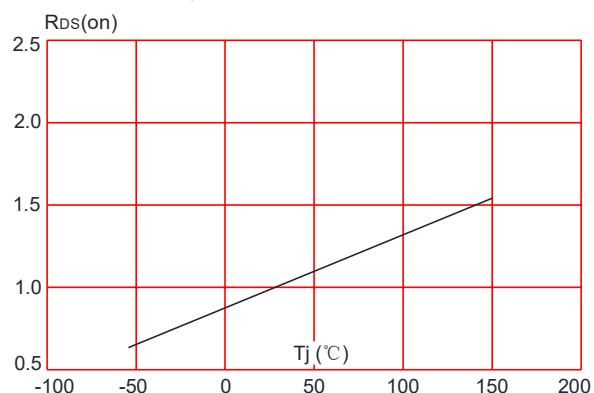
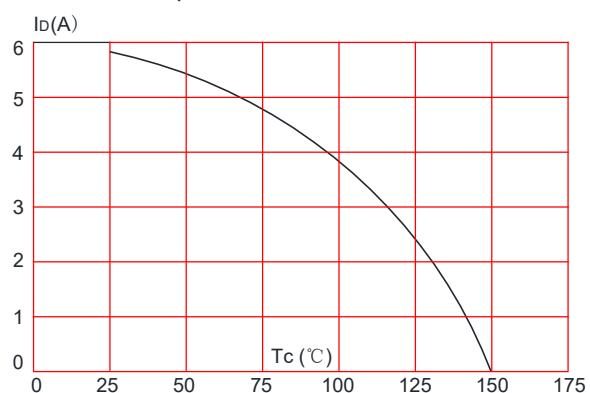


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Test Circuit

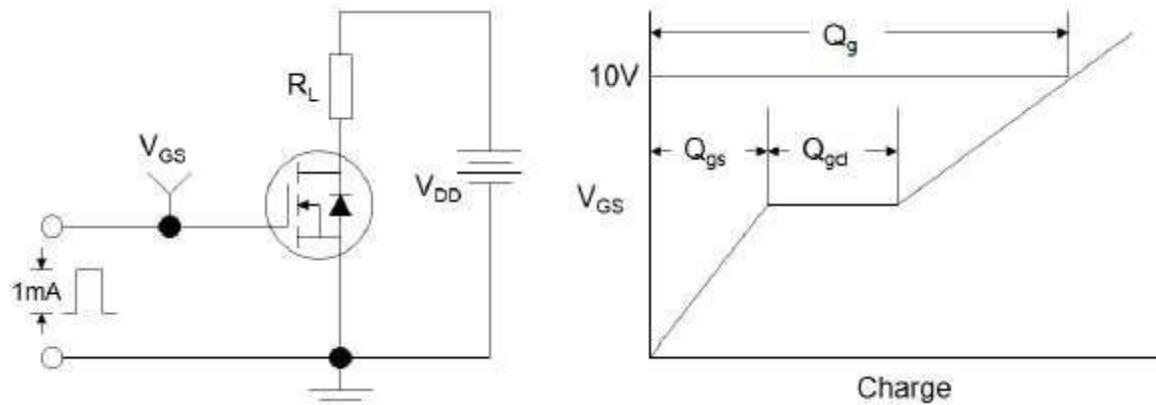


Figure1:Gate Charge Test Circuit & Waveform

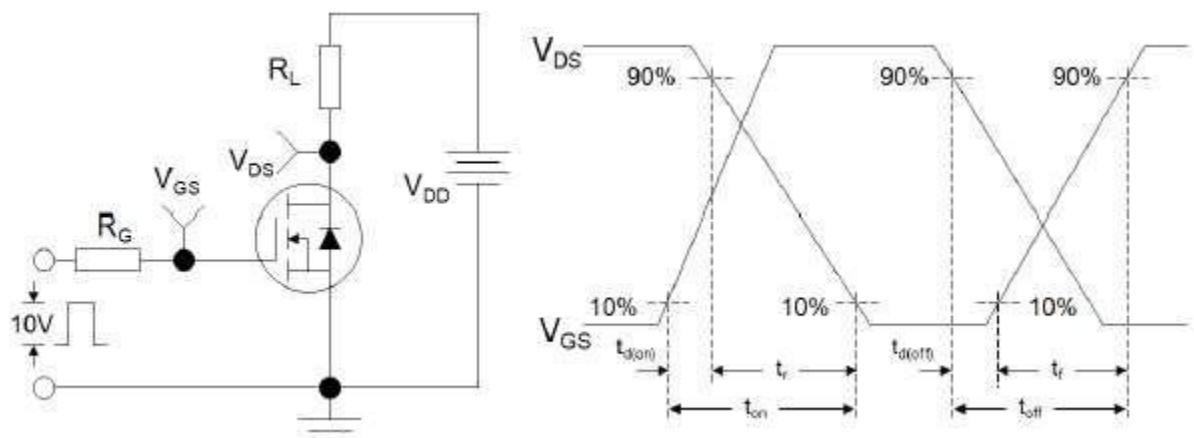


Figure 2: Resistive Switching Test Circuit & Waveforms

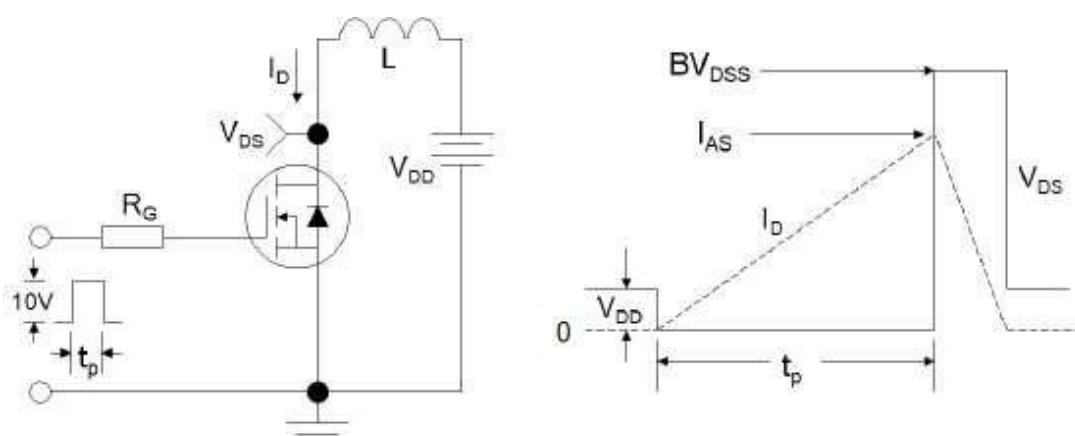
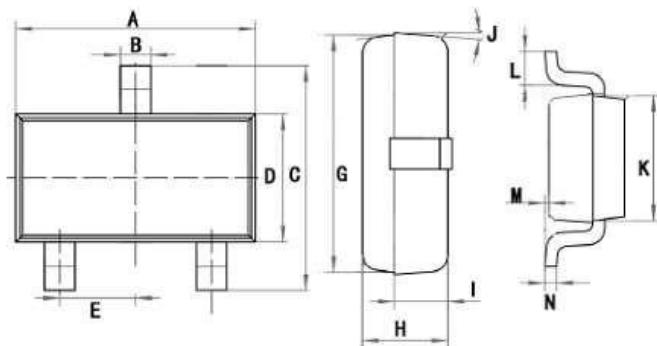


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-SOT-23-3L



A	2.90 ± 0.1	E	0.950	J	7°	N	$0.15 + 0.03$
B	0.4 ± 0.01	G	2.85 ± 0.1	K	1.550 ± 0.1		
C	2.80 ± 0.20	H	1.10 ± 0.1	L	0.40		
D	1.60 ± 0.1	I	0.70 ± 0.1	M	0.05 ± 0.03		